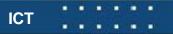
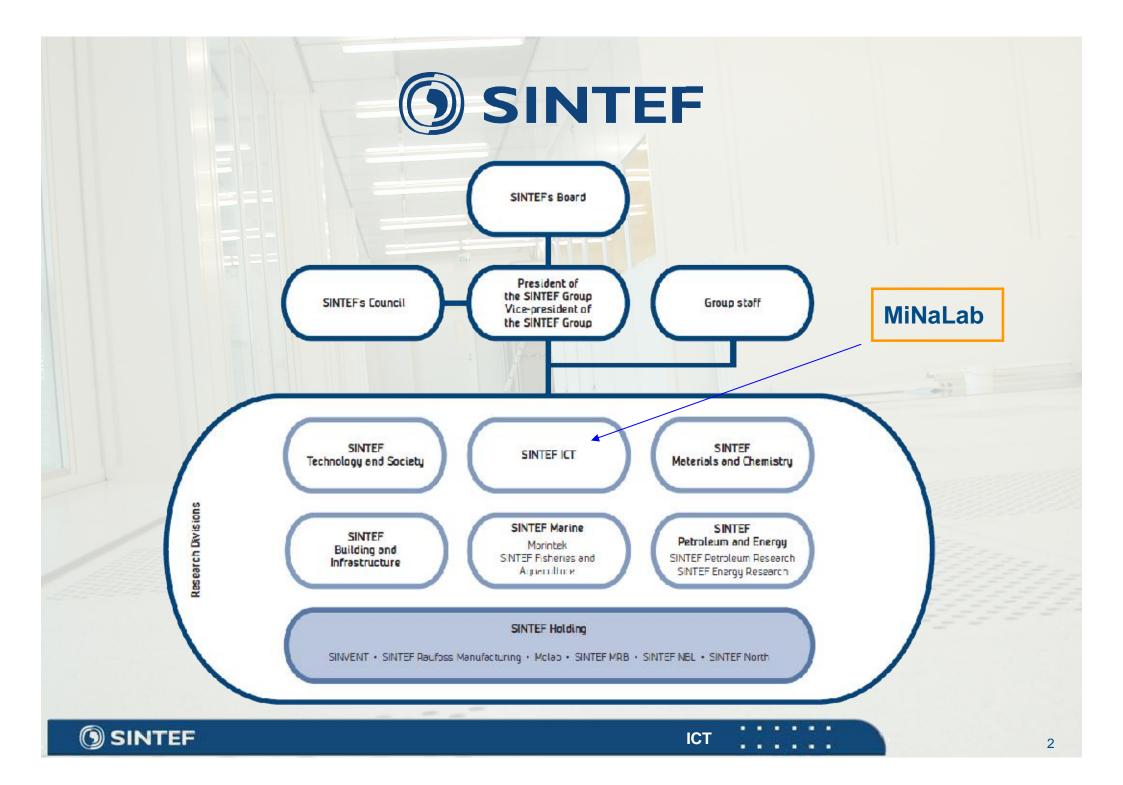
# SINTEF MiNaLab Microsystems and Nanotechnology

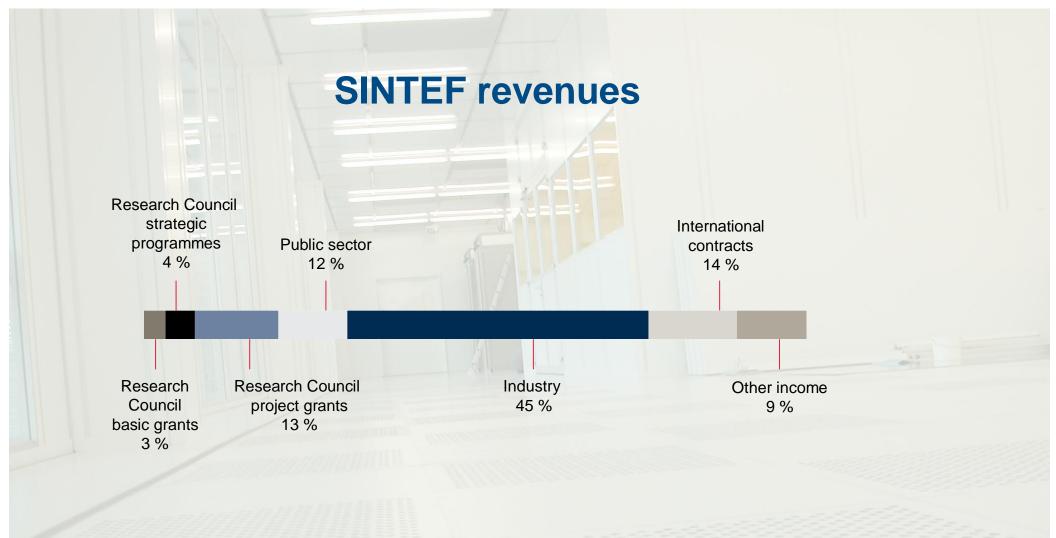
**Chief Scientist Thor-Erik Hansen** 











SINTEF turnover in 2008: NOK 2.6 billion (295 M€)





# **MiNaLab**

Turnover 2007:Turnover 2008:

53.4 MNOK (~ 6,1 M€) 58.3 MNOK (~ 6.6 M€)

- Employees:
  - Scientists:
  - Engineers:

39 28 (16 with PhD) 11

QA system approved to ISO 9001:2000





# MiNaLab (Micro- and Nanotechnology Laboratory in Oslo)





Moved into new lab in 2005

 Shared facility with the University of Oslo Two separate clean room floors: SINTEF: 800 m<sup>2</sup> University of Oslo: 600 m<sup>2</sup>

SINTEF:

 Silicon production line with annual capacity of 10.000 150 mm wafers on one shift

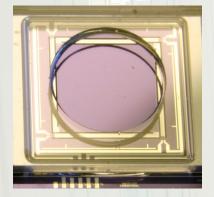
ICT

100 mm and 150 mm wafers

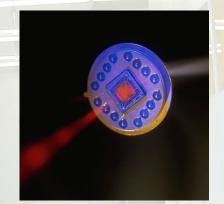
Situated on the University of Oslo campus.



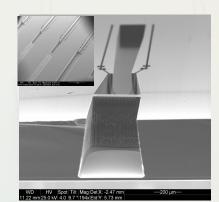
# Main research and development fields sensors and actuators



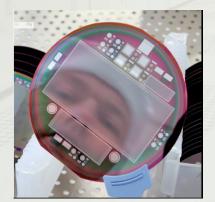
MEMS



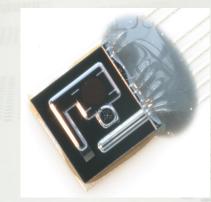
**Diffraction micro-optics** 



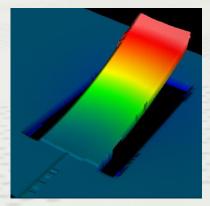
Advanced processes



**Radiation detectors** 



**Micro-fluidics** 



Functional materials (PZT)

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## **Examples of Processing Equipment**



Diffusion / oxidation furnaces
Totally 12 horizontal and 4 vertical tubes





Automatic mask aligners and coaters

- Contact / proximity printing
- Front to back-side alignment



#### Plasma tools

4 state of the art Alcatel plasma tools

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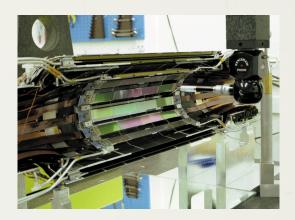
- PECVD deposition Si3N4, SiO2
- RIE and DRIE etching of silicon, SIO2, Si3N4, poly-silicon



#### **Radiation detector reference projects**

#### **High energy physics**

• Single and double sided strip detectors with AC coupling, DEPLHI micro-strip detector, CERN, 1988 -1995



- Macro-strip detectors, DELPHI tracker, CERN, 1985 -88
- Photodiodes for scintillator readout, DELPHI calorimeter, CERN, 1986-87
- Silicon drift chamber, STAR detector, Brookhaven NL, 1997-98,
- Double sided strip detectors, Athena detector, CERN, 1999 2000
- Single and double sided strip detectors, HERA B detector, DESY, 1997 -2000
- Double sided strip detectors with AC coupling, Alice detector, CERN, 2002 -2006
- Double sided pixel detectors, CMS detector, CERN, 1999 2006
- Pixel detectors, INFN Pisa /CERN, 2006 2007







#### **Radiation detector reference projects**

#### X-ray and γ- detectors

- Double sided macro-strip detectors, 2 mm thick, NRL 2005 – 2009
- Pixel detectors, 2 mm thick, NRL 2003 2005
- Pixel detectors, Cornell University, 2006 2009



- Single and double sided strip detectors with AC coupling for material analysis, non-disclosed European and US industrial customer, 2003 –
- Strip detectors for medical imaging, non-disclosed European industrial customer, 2004 -
- Edge-on detector for material analysis, non-disclosed European industrial customer, 2006 –
- XRF detector for material analysis, non-disclosed European industrial customer, 2009 –
- Drift diodes for material analysis (double sided with up to 17 mask layers), 2 non-disclosed US industrial customers, 2004 -

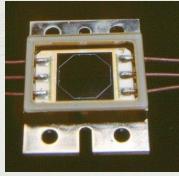
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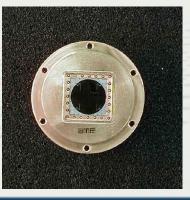
### **Radiation detector reference projects**

#### Photodiodes

- AME (OSIO Norway since 2006) has produced photodiode chips at SINTEF since 1985
- PIN diodes and quadrants for NIR (800 to 1064 nm)
- UV-, blue- and VIS- diodes, sun sensors, PSDs
- Avalanche photodiodes (APDs) for NIR (RCA structure)
- High end industrial applications, since 1987
- Defence applications, non-disclosed European defence customers, since 1987
- Space applications, Officine Galileo, Astrium, ESA / ESTEC, TNO-TPD, ISRO /SAC (India), LEOS (India), since 1989



Cryogenic Quadrant Photodiode (CQP), ISO Mission



ICT

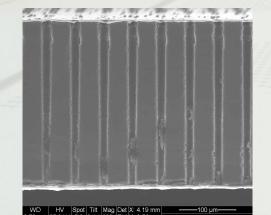
Virgo LOI Detector, SOHO Mission



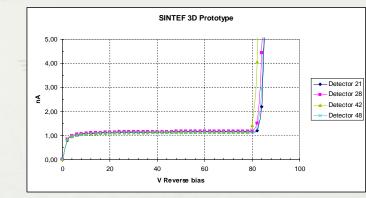
#### **Radiation detector research project**

#### **Full 3D-detectors with active edge**

- Detector chips with vertical n- and p- electrodes, and active edge trenches filled with poly-silicon. Superior radiation hardness
- SINTEF member of 3D-consortium with Manchester U., Stanford U. / SLAC, Purdue U., Hawaii U., Prague TU.
- SINTEF 2<sup>nd</sup> lab in the world to demonstrate working prototypes of full 3D - detectors (made on n-substrates with active edge sensitive to dicing)
- 2<sup>nd</sup> lot on p-substrates currently in production. Includes ATLAS FE-I4 chips, CMS-chips, and Medipix chips on same wafer



DRIE etched 14 µm electrodes through 320 µm thick wafer on oxidized support wafer



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IV- characteristics measured on first SINTEF 3D lot. ATLAS chip with 2700 pixels. 4E configuration



11

## **Risk analysis volume production at MiNaLab**

Item	Risk	Mitigating actions
1	Combined research and volume production in same lab may to lead to conflicts and reduced efficiency	Set up dedicated production line inside lab (equipment and people)
2	Cost structure and ability to meet price targets. Problems to compete on price with dedicated production companies	<ul> <li>a) Dedicated production line</li> <li>b) Focus on special products</li> <li>c) Compete on quality and performance</li> <li>c) Form alliances to share work</li> </ul>
3	Limitations in production capacity	<ul> <li>a) Invest to remove bottle necks</li> <li>b) Outsource process steps</li> <li>c) Form alliances to share work /projects</li> </ul>

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12

# Thank you for your attention!

